

Switching Characteristics of Nonlinear Field-Effect Transistors: Gallium-Arsenide Versus Silicon

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A study of the switching properties of GaAs FET's and other nonlinear elements whose high field velocity saturates without negative differential mobility demonstrates that the high-bias switching times of GaAs are determined by velocity saturation. Silicon switches are also studied, and situations where GaAs and Si switching properties may be similar are discussed.

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